

Applications

- IEEE802.11b DSSS WLAN
- IEEE802.11g,n OFDM WLAN
- Embedded applications

Features

- □ Integrates SP3T Switch and LNA with by-pass mode
- 12 dB gain,
- □ 1.8 dB NF
- □ 0.5 dB Bluetooth path loss
- 1.07x1.05x 0.38mm, 250 um pitch, SnAg solder bump
- □ Lead free, Halogen free and RoHS compliant

Product Description

The SE2600S is a single chip integrated front-end module (FEM) with a Bluetooth port to complement WLAN chipsets with integrated Power Amplifier. The FEM integrates SP3T Switch and Low Noise Amplifier with bypass mode in an ultra compact package. It is capable of switching between WLAN RX, WLAN TX and Bluetooth™

Ordering Information

Part No.	Package	Remark
SE2600S	11 pin CSP	Samples
SE2600S-R	11 pin CSP	Tape and Reel
SE2600S-EK1	N/A	Evaluation kit

Functional Block Diagram

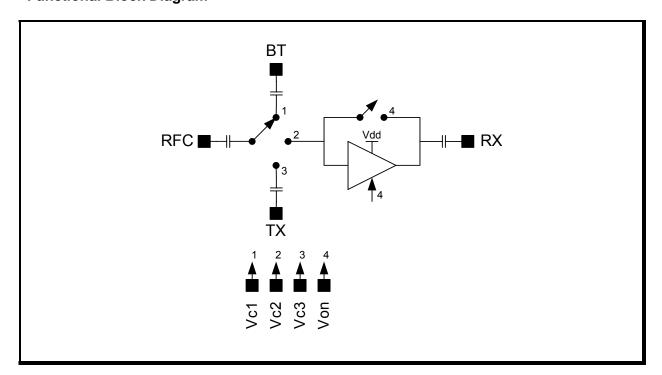


Figure 1: Functional Block Diagram



http://www.sige.com

Email: sales@sige.com

Customer Service Locations:

North America: Hong Kong

 1050 Morrison Drive, Suite 100
 Phone: +852 3428 7222

 Ottawa ON K2H 8K7 Canada
 Fax: +852 3579 5450

Phone: +1 613 820 9244 San Diego

Fax: +1 613 820 4933 Phone: +1 858 668 3541 (ext. 226)

Fax: +1 858 668 3546

United Kingdom

Phone: +44 1279 464217 Fax: +44 1279 464201

Product Preview

The datasheet contains information from the product concept specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Preliminary Information

The datasheet contains information from the design target specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Production testing may not include testing of all parameters.

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